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Team Nexperia

PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

Rev. 5 — 12 November 2013

Product data sheet

1. Product profile

1.1 General description

NPN/NPN double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package		PNP/PNP	NPN/PNP	Package
	NXP	JEITA	complement	complement	configuration
PEMH9	SOT666	-	PEMB9	PEMD9	ultra small and flat lead
PIMH9	SOT457	SC-74	-	-	small
PUMH9	SOT363	SC-88	PUMB9	PUMD9	very small

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
 - Reduces pick and place costs
 - AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor					
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
Io	output current		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	



2. Pinning information

Table 3. Pinning

Table 3.	riiiiiig		
Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1 R1 1 2 3
			sym063

3. Ordering information

Table 4. Ordering information

Type number	Package				
	Name	Description	Version		
PEMH9	-	plastic surface-mounted package; 6 leads	SOT666		
PIMH9	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457		
PUMH9	SC-88	plastic surface-mounted package; 6 leads	SOT363		

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMH9	H9
PIMH9	H9
PUMH9	H*9

^{[1] * =} placeholder for manufacturing site code

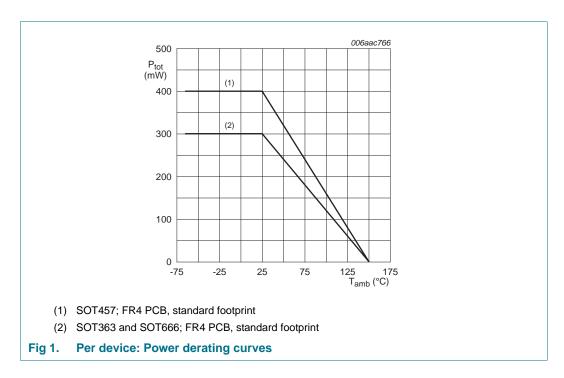
5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
VI	input voltage				
	positive		-	+40	V
	negative		-	-6	V
Io	output current		-	100	mA
I _{CM}	peak collector current	$\begin{array}{l} \text{single pulse;} \\ t_p \leq 1 \text{ ms} \end{array}$	-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMH9 (SOT666)		<u>[1]</u> -	200	mW
	PIMH9 (SOT457)		<u>[1]</u>	250	mW
	PUMH9 (SOT363)		<u>[1]</u> -	200	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMH9 (SOT666)		<u>[1]</u> -	300	mW
	PIMH9 (SOT457)		<u>[1]</u>	400	mW
	PUMH9 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		–55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

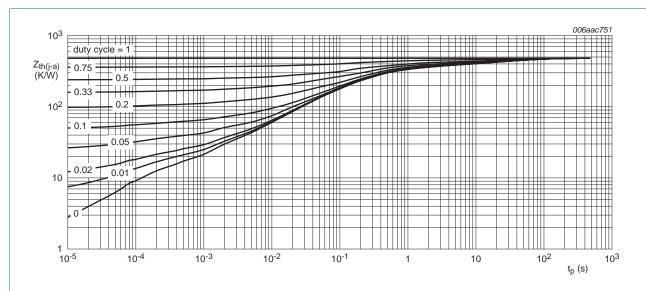


6. Thermal characteristics

Table 7. Thermal characteristics

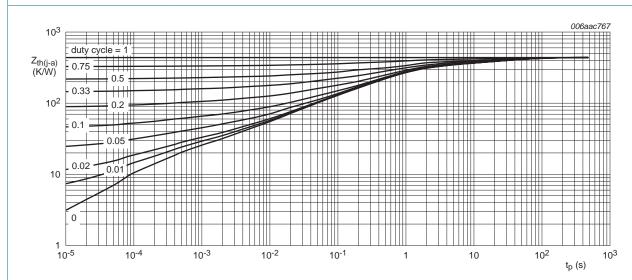
Parameter	Conditions	Min	Тур	Max	Unit
or					
thermal resistance from junction to ambient	in free air				
PEMH9 (SOT666)		[1] -	-	625	K/W
PIMH9 (SOT457)		[1] -	-	500	K/W
PUMH9 (SOT363)		<u>[1]</u> -	-	625	K/W
thermal resistance from junction to ambient	in free air				
PEMH9 (SOT666)		<u>[1]</u> -	-	417	K/W
PIMH9 (SOT457)		<u>[1]</u> _	-	313	K/W
PUMH9 (SOT363)		[1] -	-	417	K/W
	thermal resistance from junction to ambient PEMH9 (SOT666) PIMH9 (SOT457) PUMH9 (SOT363) thermal resistance from junction to ambient PEMH9 (SOT666) PIMH9 (SOT457)	thermal resistance from in free air junction to ambient PEMH9 (SOT666) PIMH9 (SOT363) thermal resistance from in free air junction to ambient PEMH9 (SOT666) PIMH9 (SOT666) PIMH9 (SOT457)	thermal resistance from junction to ambient PEMH9 (SOT666) PIMH9 (SOT457) PUMH9 (SOT363) thermal resistance from junction to ambient PEMH9 (SOT666) PIMH9 (SOT666) PIMH9 (SOT457) 11 -	thermal resistance from junction to ambient PEMH9 (SOT666) PIMH9 (SOT457) PUMH9 (SOT363) thermal resistance from junction to ambient PEMH9 (SOT666) PIMH9 (SOT666) PIMH9 (SOT457) 11 11	thermal resistance from junction to ambient PEMH9 (SOT666)

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



FR4 PCB, standard footprint

Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PEMH9 (SOT666); typical values



FR4 PCB, standard footprint

Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PIMH9 (SOT457); typical values

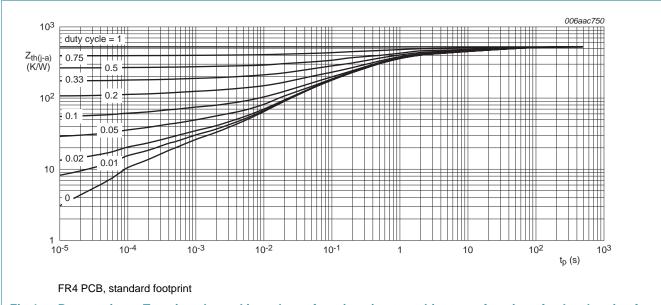


Fig 4. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMH9 (SOT363); typical values

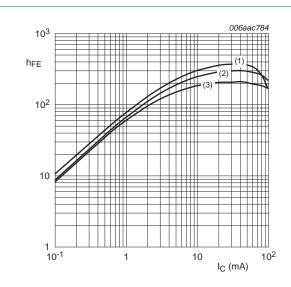
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
Per trans	sistor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	100	nA
	current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	150	μΑ
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	100	0 -	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$	-	-	100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	0.7	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 1 \text{ mA}$	1.4	0.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF
f _T	transition frequency	$V_{CE} = 5 \text{ V; } I_{C} = 10 \text{ mA;}$ f = 100 MHz	[1] -	230	-	MHz

^[1] Characteristics of built-in transistor



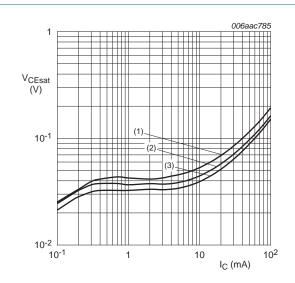
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. DC current gain as a function of collector current; typical values



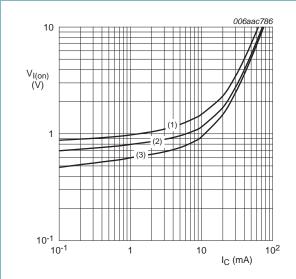
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 6. Collector-emitter saturation voltage as a function of collector current; typical values



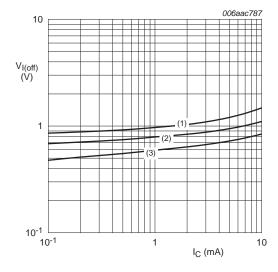
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 8. Off-state input voltage as a function of collector current; typical values

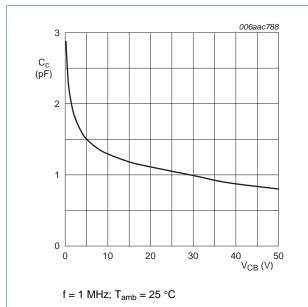


Fig 9. Collector capacitance as a function of collector-base voltage; typical values

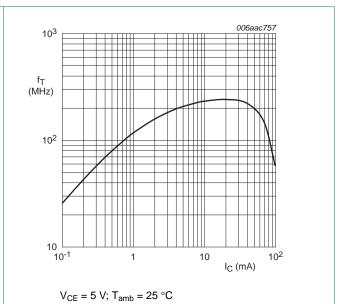


Fig 10. Transition frequency as a function of collector current; typical values of built-in transistor

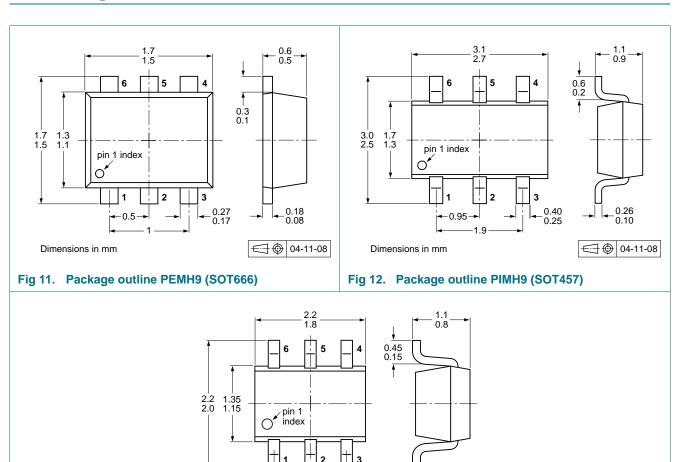
8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

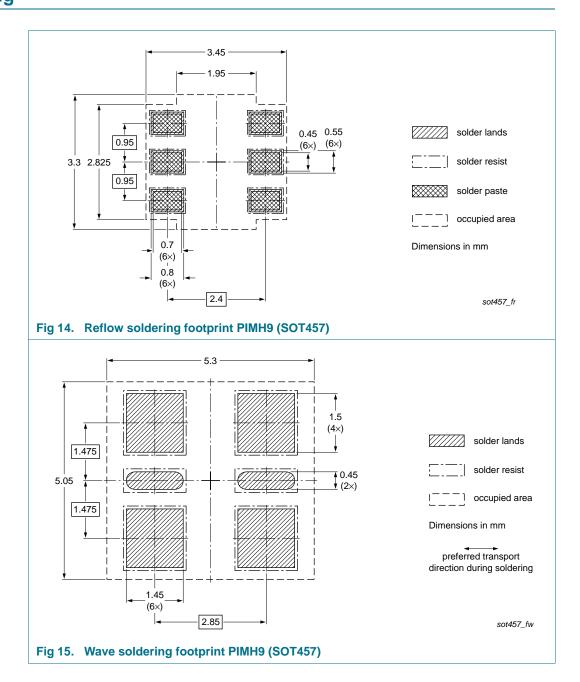
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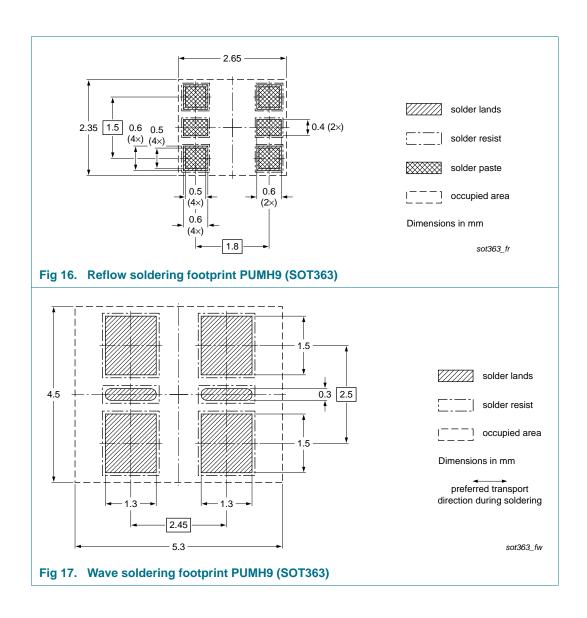
9. Package outline

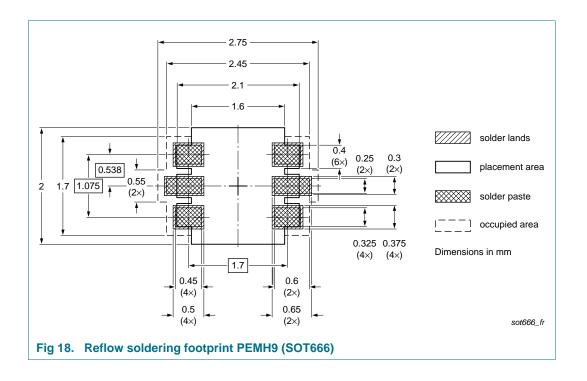


Dimensions in mm

10. Soldering







NPN/NPN resistor-equipped transistors; R1 = 10 kΩ, R2 = 47 kΩ

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PEMH9_PIMH9_PUMH9 v.5	20131112	Product data sheet	-	PIMH9_PUMH9_PEMH9 v.4		
Modifications: • The format of this document has been redesigned to comply with the new guidelines of NXP Semiconductors.						
	 Legal texts h 	ave been adapted to the new	company na	ame where appropriate.		
	 Section 1 "P 	roduct profile": updated				
	 Section 4 "M 	larking": updated				
	 Figure 1 to 1 	<u>0</u> : added				
	 Section 5 "Li 	miting values": updated				
	 Section 6 "TI 	hermal characteristics": updat	ed			
	 Table 8 "Cha 	aracteristics": V _{i(on)} redefined to	o V _{I(on)} on-st	/ _{I(on)} on-state input voltage, V _{i(off)} redefined		
	to V _{I(off)} off-s	tate input voltage, I _{CEO} update	ed, f _T added			
	 Section 8 "Te 	est information": added				
	 Section 9 "Page 12" 	ackage outline": superseded b	y minimized	I package outline drawings		
	 Section 10 "S 	Soldering": added				
	 Section 12 "I 	Legal information": updated				
PIMH9_PUMH9_PEMH9 v.4	20040414	Product data sheet	-	PIMH9_PUMH9_PEMH9 v.3		
PIMH9_PUMH9_PEMH9 v.3	20030915	Product specification		-		

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PEMH9_PIMH9_PUMH9

PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

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PEMH9; PIMH9; PUMH9

NPN/NPN resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

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